# PA83 - PA83A POWER OPERATIONAL AMPLIFIERS

#### **FEATURES**

- LOW BIAS CURRENT, LOW NOISE FET Input
- PROTECTED OUTPUT Thermal Shutoff
- FULLY PROTECTED INPUT Up to ±150V
- WIDE SUPPLY RANGE ±15V to ±150V
- ◆ SECOND SOURCEABLE BB3583AM/JM

#### **APPLICATIONS**

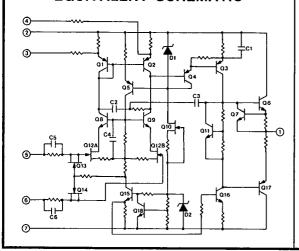
- HIGH VOLTAGE INSTRUMENTATION
- ELECTROSTATIC TRANSDUCERS & DEFLECTION
- **◆ PROGRAMMABLE POWER SUPPLIES UP TO 290V**
- ANALOG SIMULATORS

#### DESCRIPTION

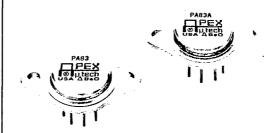
The PA83 is a high voltage operational amplifier designed for output voltage swings up to ±145V with a dual (±) supply or 290V with a single supply. Its input stage is protected against transient and steady state overvoltages up to and including the supply rails. High accuracy is achieved with a cascode input circuit configuration. All internal biasing is referenced to a zener diode fed by a FET constant current source. As a result, the PA83 features an unprecedented supply range and excellent supply rejection. The output stage is biased in the class A/B mode for linear operation. Internal phase compensation assures stability at all gain settings without need for external components. Fixed current limits protect these amplifiers against shorts to common at supply voltages up to 120V. For operation into inductive loads, two external flyback pulse protection diodes are recommended. A built-in thermal shutoff circuit prevents destructive overheating. However, a heatsink may be necessary to maintain the proper case temperature under normal operating conditions.

This hybrid circuit utilizes beryllia (BeO) substrates, thick (cermet) film resistors, ceramic capacitors and silicon semiconductor chips to maximize reliability, minimize size and give top performance. Ultrasonically bonded aluminum wires provide reliable interconnections at all operating temperatures. The 8 pin TO-3 package is hermetically sealed and electrically isolated. The use of compressible washers may void the warranty.

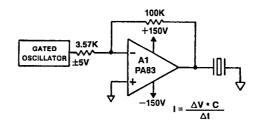
#### **EQUIVALENT SCHEMATIC**



# T-79-23



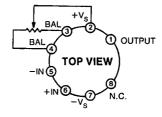
### TYPICAL APPLICATION



#### SIMPLE PIEZO ELECTRIC TRANSDUCER DRIVE

While piezo electric transducers present a complex impedance, they are often primarily capacitive at useful frequencies. Due to this capacitance, the speed limitation for a given transducer/amplifier combination may well stem from limited current drive rather than power bandwidth restrictions. With its drive capability of 75mA, the PA83 can drive transducers having up to 2nF of capacitance at 40kHz at maximum output voltage. In the event the transducer may be subject to shock or vibration, flyback diodes, voltage clamps or other protection networks must be added to protect the amplifier from high voltages which may be generated.

#### **EXTERNAL CONNECTIONS**



NOTES: 1. Pin 8 not internally connected.

2. Input offset trimpot optional. Recommended value  $100 \text{K}\Omega$ 

# PA83 ABSOLUTE MAXIMUM RATINGS

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SUPPLY VOLTAGE, +Vs to -Vs	300V
OUTPUT CURRENT, within SOA	Internally Limited
POWER DISSIPATION, internal at T <sub>c</sub> = 25° C <sup>1</sup>	17.5W
INPUT VOLTAGE, differential	±300V
INPUT VOLTAGE, common-mode	±300V
TEMPERATURE, pin solder-10s max (solder)	300°C
TEMPERATURE, junction	150°C
TEMPERATURE RANGE, storage	−65 to +150°C
OPERATING TEMPERATURE RANGE, case	-55 to +125°C

# **SPECIFICATIONS**

		P/	A83/PA83	3J		PA83A				
PARAMETER	TEST CONDITIONS2	MIN	TYP	MAX	MIN	TYP	MAX	UNITS		
INPUT										
OFFSET VOLTAGE, initial OFFSET VOLTAGE, vs. temperature OFFSET VOLTAGE, vs. supply OFFSET VOLTAGE, vs. time BIAS CURRENT, initial <sup>3</sup> BIAS CURRENT, vs. supply OFFSET CURRENT, initial <sup>3</sup> OFFSET CURRENT, vs. supply INPUT IMPEDANCE, dc INPUT CAPACITANCE COMMON-MODE VOLTAGE RANGE <sup>4</sup>	$T_{c}=25^{\circ}\text{C}$ Full temperature range $T_{c}=25^{\circ}\text{C}$ $T_{c}=25^{\circ}\text{C}$ $T_{c}=25^{\circ}\text{C}$ $T_{c}=25^{\circ}\text{C}$ $T_{c}=25^{\circ}\text{C}$ $T_{c}=25^{\circ}\text{C}$ $T_{c}=25^{\circ}\text{C}$ $T_{c}=25^{\circ}\text{C}$ $T_{c}=25^{\circ}\text{C}$ Full temperature range Full temperature range	±Vs −10		±3 ±25 50 ±50	*	±.5 ±5 ±.2 3 ±1.5	±1 ±10 10 ±10	mV μV/° C μV/V μV/√kh pA pA/V pA pA/V Ω pF V		
COMMON-MODE REJECTION, dc	Full temperature range	<u> </u>	130			L	<u></u>	db		
$ \begin{array}{lll} \text{OPEN LOOP GAIN at 10Hz} & \text{$T_c = 25^{\circ}\text{C}, \; R_L = 2K\Omega$} \\ \text{UNITY GAIN CROSSOVER FREQ.} & \text{$T_c = 25^{\circ}\text{C}, \; R_L = 2K\Omega$} \\ \text{POWER BANDWIDTH} & \text{$T_c = 25^{\circ}\text{C}, \; R_L = 10K\Omega$} \\ \text{PHASE MARGIN} & \text{Full temperature range} \\ \end{array} $		96	116 5 60 60		* 3 40	* * *		db MHz kHz		
OUTPUT	1 /	1	L*-	l		1	1	L		
VOLTAGE SWING <sup>4</sup> , full load VOLTAGE SWING <sup>4</sup> CURRENT, peak CURRENT, short circuit SLEW RATE <sup>9</sup> CAPACITIVE LOAD, unity gain CAPACITIVE LOAD, gain>4 SETTLING TIME to 0.1%	Full temp. range, $I_0=75 mA$ Full temp. range, $I_0=15 mA$ $T_c=25^{\circ}C$ $T_c=25^{\circ}C$ $T_c=25^{\circ}C$ , $R_L=2K\Omega$ Full temperature range Full temperature range $T_c=25^{\circ}C$ , $R_L=2K\Omega$ , $10V$ step	±V <sub>s</sub> -10 ±V <sub>s</sub> -5 75 20	±V <sub>s</sub> -5 ±V <sub>s</sub> -3 100 30	10 SOA	* * *	* * *	* *	V V mA mA V/μs nF μF μs		
POWER SUPPLY										
		±15	±150 6	±150 8.5	*	*	*	V mA		
THERMAL										
RESISTANCE, ac <sup>5</sup> junction to case RESISTANCE, dc junction to case RESISTANCE, case to air TEMP. RANGE, case (PA83/PA83A) TEMP. RANGE, case (PA83J)  Meets full range specification Meets full range specification		-25 0	3.8 6 30	6.5 +85 70	*	* *	*	°C/W °C/W °C/W		

# NOTES:

- \* The specification of PA83A is identical to the specification for PA83 in applicable column to the left.

  1. Long term operation at the maximum junction temperature will result in reduced product life. Derate internal power dissipation to achieve high MTTF.
- 2. The power supply voltage for all tests is the TYP rating unless otherwise specified as a test condition.
- 3. Doubles for every 10°C of temperature increase

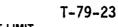
- 4. +V<sub>S</sub> and -V<sub>S</sub> denote the positive and negative supply rail respectively.
  5. Rating applies if the output current alternates between both output transistors at a rate faster than 60Hz.
  6. Signal slew rates at pins 5 and 6 must be limited to less than 1V/ns to avoid damage. When faster waveforms are unavoidable,

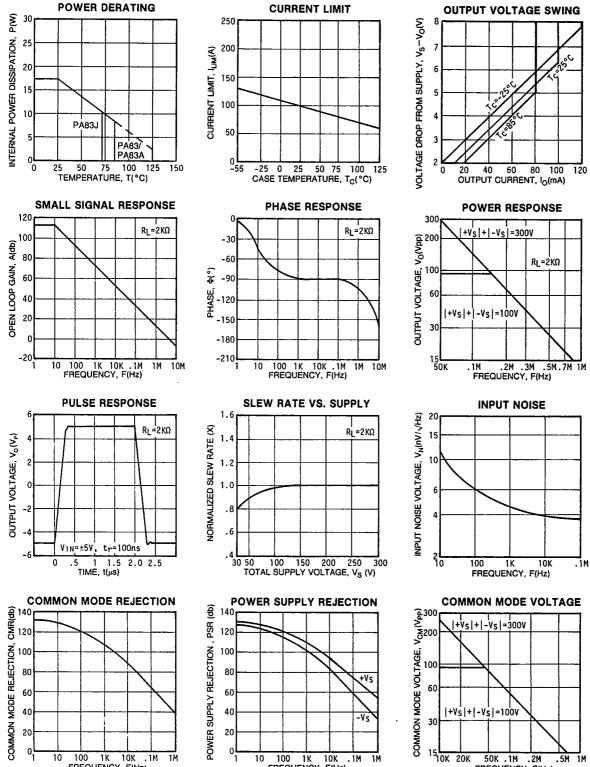
CAUTION:

resistors in series with those pins, limiting current to 150mA will protect the amplifier from damage.

The internal substrate contains beryllia (BeO). Do not break the seal. If accidently broken, do not crush, machine, or subject to temperatures in excess of 850°C to avoid generating toxic fumes.

# **PA83 TYPICAL PERFORMANCE GRAPHS**





FREQUENCY, F(Hz)

FREQUENCY, F(Hz)

117

FREQUENCY, F(Hz)

## T-79-23

#### **GENERAL**

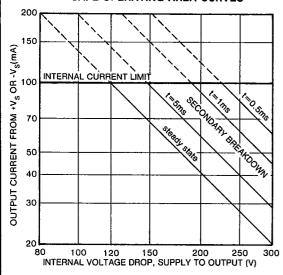
Please read the "General Operating Considerations" section, which covers stability, supplies, heatsinking, mounting, current limit, SOA interpretation, and specification interpretation. Additional information can be found in the applications notes. For information on the package outline, heatsinks, and mounting hardware, consult the "Accessory and Package Mechanical Data" section of the handbook.

#### SAFE OPERATING AREA (SOA)

The bipolar output stage of this high voltage amplifier has two distinct limitations:

- The internal current limit, which limits maximum available output current.
- The secondary breakdown effect, which occurs whenever the simultaneous collector current and callector-emitter voltage exceed specified limits.

#### SAFE OPERATING AREA CURVES



The SOA curves combine the effect of these limits. For a given application, the direction and magnitude of the output current should be calculated or measured and checked against the SOA curves. This is simple for resistive loads but more complex for reactive and EMF generating loads. However, the following guidelines may save extensive analytical efforts:

1. The following capacitive and inductive loads are safe:

C(MAX)	L(MAX)
.7μF	` 1.5H
2.0μF	2.5H
5.0μF	6.0H
60µF	30H
ALL	ALL
	.7μF 2.0μF 5.0μF 60μF

- 2. Short circuits to ground are safe with dual supplies up to  $\pm 120\text{V}$  or single supplies up to 120V.
- Short circuits to the supply rails are safe with total supply voltages up to 120V. (ie ±60V).
- The output stage is protected against transient flyback. However, for protection against sustained, high energy flyback, external fast-recovery diodes should be used.

#### THERMAL SHUTDOWN PROTECTION

The thermal protection circuit shuts off the amplifier when the sustrate temperature exceeds approximately 150°C. This allows heatsink selection to be based on normal operating conditions while protecting the amplifier against excessive jucntion temperature during temporary fault conditions.

Thermal protection is a fairly slow-acting circuit and therefore does not protect the amplifier against transient SOA violations (areas outside of the  $T_{\rm C}=25^{\circ}{\rm C}$  boundary). It is designed to protect against short-term fault conditions that result in high power dissipation within the amplifier. If the conditions that cause thermal shutdown are not removed, the amplifier will oscillate in and out of shutdown. This will result in high peak power stresses, destroy signal integrity, and reduce the reliability of the device.

#### INDUCTIVE LOADS

Two external diodes as shown in figure 1, are required to protect these amplifiers against flyback (kickback) pulses exceeding the supply voltages of the amplifier when driving inductive loads. For component selection, these external diodes must be very quick, such as ultra fast recovery diodes with no more than 200 nanoseconds of reverse recovery time. The diode will turn on to divert the flyback energy into the supply rails thus protecting the output transistors from destruction due to reverse bias.

A note of caution about the supply. The energy of the flyback pulse must be absorbed by the power supply. As a result, a transient will be superimposed on the supply voltage, the magnitude of the transient being a function of its transient impedance and current sinking capability. If the supply voltage plus transient exceeds the maximum supply rating or if the AC impedance of the supply is unknown, it is best to clamp the output and the supply with a zener diode to absorb the transient.

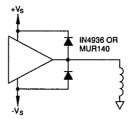


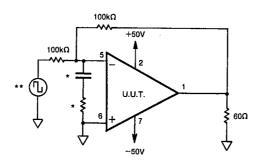
FIGURE 1. PROTECTION, INDUCTIVE LOAD.

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SG		SYMBOL	TEMP	PWR	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent Current	la la	25°C	±150V	V <sub>IN</sub> = 0, G = 100		8.5	mA
1	Input Offset Voltage	Vos	25°C	±150V	$V_{IN} = 0$ , $G = 100$		3	m∨
1	Input Offset Voltage	Vos	25°C	±15V	$V_{IN} = 0, G = 100$	l	5.7	m∨
1	Input Bias Current, +IN	+l <sub>B</sub>	25°C	±150V	V <sub>IN</sub> = 0, G = 100		50	pA .
1	Input Bias Current, -IN	−I <sub>B</sub>	25°C	±150V	$V_{IN} = 0$ , $G = 100$		50	pΑ
1	Input Offset Current	los	25°C	±150V	$V_{IN} = 0, G = 100$		50	pΑ
3	Quiescent Current	la	-55°C	±150V	V <sub>IN</sub> = 0, G = 100		10	mA
3	Input Offset Voltage	Vos	55°C	±150V	V <sub>IN</sub> = 0, G = 100		5	m∨
3	Input Offset Voltage	Vos	−55°C	±15V	$V_{IN} = 0, G = 100$		7.7	mV
3	Input Bias Current, +IN	+l <sub>B</sub>	−55°C	±150V	$V_{iN} = 0, G = 100$		50	pΑ
3	Input Bias Current, -IN	—ł <sub>8</sub>	−55°C	±150V	V <sub>IN</sub> = 0, G = 100	ſ	50	pA
3	Input Offset Current	los	−55°C	±150V	$V_{IN} = 0$ , $G = 100$		50	pΑ
2	Quiescent Current	l <sub>o</sub>	125°C	±150V	V <sub>IN</sub> = 0, G = 100		10	mA
2	Input Offset Voltage	Vos	125°C	±150V	V <sub>IN</sub> = 0, G = 100		5.5	mV
2	Input Offset Voltage	Vos	125°C	±15V	V <sub>IN</sub> = 0, G = 100		8.2	mV
2	Input Bias Current, +IN	+16	125°C	±150V	V <sub>IN</sub> = 0, G = 100		10	nA
2	Input Bias Current, -IN	-l <sub>B</sub>	125°C	±150V	V <sub>IN</sub> = 0, G = 100		10	пA
2	Input Offset Current	los	125°C	±150V	V <sub>IN</sub> = 0, G = 100		10	nA
4	Output Voltage, Io = 75mA	Vo	25°C	±85V	R <sub>L</sub> = 1K	75		V
4	Output Voltage, Io = 29mA	V <sub>o</sub>	25°C	±150V	R <sub>L</sub> = 5K	145		l v l
4	Current Limits	l <sub>CL</sub>	25°C	±30V	$R_L = 100\Omega$	75	125	mA
4	Stability/Noise	En	25°C	±150V	R <sub>L</sub> = 5K, G = 1, C <sub>L</sub> = 10nF		1	mV
4	Slew Rate	SR	25°C	±150V	R <sub>L</sub> = 5K	20	60	V/μs
4	Open Loop Gain	Aol	25°C	±150V	R <sub>L</sub> = 5K, f = 10Hz	96		db
4	Common-mode Rejection	CMR	25°C	±32.5V	$R_{L_i} = 5K$ , $f = DC$ , $V_{CM} = \pm 22.5V$	90		db
6	Output Voltage, Io = 40mA	Vo	−55°C	±45V	R <sub>L</sub> = 1K	40		v
6	Output Voltage, Io = 29mA	Vo	-55°C	±150V	RL = 5K	145		v
6	Stability/Noise	En	−55°C	±150V	R <sub>L</sub> = 5K, G = 1, C <sub>L</sub> = 10nF	140	1	mV
6	Slew Rate	SR	−55°C	±150V	R <sub>L</sub> = 5K	20	60	V/μs
	Open Loop Gain	AoL	-55°C	±150V	$R_L = 5K$ , $f = 10Hz$	96	OU.	V/μs db
	Common-mode Rejection	CMR	−55°C	±32.5V	$R_L = 5K, f = DC, V_{CM} = \pm 22.5V$	90		db
5	Output Voltage, Io = 40mA	Vo	125°C	±45V	R <sub>L</sub> = 1K	40		
_	Output Voltage, lo = 29mA	V <sub>0</sub>	125°C	±150V	R <sub>L</sub> = 5K			V
	Stability/Noise	E <sub>N</sub>	125°C	±150V	RL = 5K   RL = 5K, G = 1, CL = 10nF	145		٧
-	Slew Rate	SR	125°C	±150V	R <sub>L</sub> = 5K	00	1	m۷
	Open Loop Gain	AoL	125°C	±150V	$R_L = 5K$ $R_L = 5K$ , $f = 10Hz$	20	60	V/μs
	Common-mode Rejection	CMR	125°C	±32.5V	$H_L = 5K, f = 10Hz$ $H_L = 5K, f = DC, V_{CM} = \pm 22.5V$	96		db
		CIVIT	123 0	T02.5V	nt - 3r, i = DC, vcm = ±22.5V	90		db

### **BURN IN CIRCUIT:**

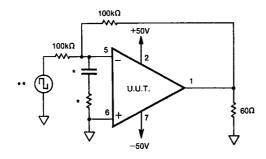


<sup>\*</sup>These components are used to stabilize device due to poor high frequency characteristics of burn in board.

<sup>\*\*</sup>Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.

	<b>Estrib</b> il			1	-79-23 <b>1</b> 0	0% TE	ST T	BELE:
SG	PARAMETER	SYMBOL	TEMP	PWR	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent Current	l <sub>a</sub>	25°C	±150V	$V_{IN} = 0$ , $G = 100$		8.5	mA
1	Input Offset Voltage	Vos	25°C	±150V	$V_{IN} = 0$ , $G = 100$		3	mV
1	Input Offset Voltage	Vos	25°C	±15V	$V_{IN} = 0, G = 100$		5.7	mV
1	Input Bias Current, +IN	+l <sub>B</sub>	25°C	±150V	$V_{IN} = 0, G = 100$	]	50	pΑ
1	Input Bias Current, -IN	I <sub>B</sub>	25°C	±150V	$V_{IN} = 0$ , $G = 100$	1	50	pΑ
1	Input Offset Current	los	25°C	±150V	$V_{IN} = 0, G = 100$		50	pA .
3	Quiescent Current	la	−25°C	±150V	V <sub>IN</sub> = 0, G = 100		10	mA
3	Input Offset Voltage	Vos	−25°C	±150V	$V_{IN} = 0, G = 100$		4.2	mV
3	Input Offset Voltage	Vos	−25°C	±15V	$V_{iN} = 0$ , $G = 100$		6.9	m۷
3	Input Bias Current, +IN	+18	−25°C	±150V	$V_{IN} = 0$ , $G = 100$		50	pΑ
3	Input Bias Current, -IN	—I <sub>B</sub>	−25°C	±150V	$V_{IN} = 0, G = 100$		50	pΑ
3	Input Offset Current	los	−25°C	±150V	V <sub>IN</sub> = 0, G = 100		50	pA
2	Quiescent Current	la	85°C	±150V	V <sub>IN</sub> = 0, G = 100		10	mA
2	Input Offset Voltage	Vos	85°C	±150V	$V_{IN} = 0$ , $G = 100$		4.5	mV
2	Input Offset Voltage	Vos	85°C	±15V	$V_{IN} = 0, G = 100$		7.2	mV
2	Input Bias Current, +IN	+l <sub>B</sub>	85°C	±150V	$V_{IN} = 0$ , $G = 100$	1	3.2	nΑ
2	Input Bias Current, -IN	-l <sub>B</sub>	85°C	±150V	$V_{IN} = 0$ , $G = 100$		3.2	nA
2	Input Offset Current	los	85°C	±150V	V <sub>IN</sub> = 0, G = 100		3.2	nA
4	Output Voltage, Io = 75mA	Vo	25°C	±85V	R <sub>L</sub> = 1K	75		V
4	Output Voltage, Io = 75mA	Vo	25°C	±85V	R <sub>L</sub> = 5K	145		V
4	Current Limits	lcu	25°C	±30V	$R_L = 100\Omega$	75	125	mA
4	Stability/Noise	EN	25°C	±150V	$R_L = 5K, G = 1, C_L = 10nF$		1	m۷
4	Slew Rate	SR	25°C	±150V	R <sub>L</sub> = 5K	20	60	V/μs
4	Open Loop Gain	AoL	25°C	±150V	R <sub>L</sub> = 5K, f = 10Hz	96		db
4	Common-mode Rejection	CMR	25°C	±32V	$R_L = 5K, f = DC, V_{CM} = \pm 22.5V$	90		db
6	Output Voltage, Io = 55mA	V <sub>o</sub>	−25°C	±65V	R <sub>L</sub> = 1K	3		V
6	Output Voltage, Io = 29mA	V <sub>o</sub>	−25°C	±150V	R <sub>L</sub> = 5K	145		V
6	Stability/Noise	E <sub>N</sub>	−25°C	±150V	$R_L = 5K, G = 1, C_L = 10nF$	1	1	mV
6	Slew Rate	SR	−25°C	±150V	R <sub>L</sub> = 5K	20	60	V/μs
6	Open Loop Gain	Aol	-25°C	±150V	R <sub>L</sub> = 5K, f = 10Hz	96		db
6	Common-mode Rejection	CMR	−25°C	±32V	$R_L = 5K, f = DC, V_{CM} = \pm 22.5V$	90		db
5	Output Voltage, Io = 55mA	∣ v₀	85°C	±65V	R <sub>L</sub> = 1K	55		٧
5	Output Voltage, Io = 29mA	V <sub>o</sub>	85°C	±150V	R <sub>L</sub> = 5K	145		٧
5	Stability/Noise	E <sub>N</sub>	85°C	±150V	$R_L = 5K, G = 1, C_L = 10nF$	1	1	mV
5	Slew Rate	SR	85°C	±150V	$R_L = 5K$	20	60	V/μs
5	Open Loop Gain	Aol	85°C	±150V	R <sub>L</sub> = 5K, f = 10Hz	96	1	db
5	Common-mode Rejection	CMR	85°C	±32V	$R_L = 5K, f = DC, V_{CM} = \pm 22.5V$	90	<u> </u>	db

#### **BURN IN CIRCUIT:**



<sup>\*</sup>These components are used to stabilize device due to poor high frequency characteristics of burn in board.

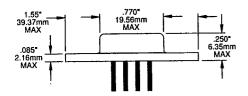
<sup>\*\*</sup>Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.

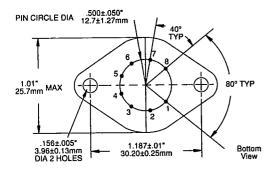
# PACKAGE OUTLINE DIMENSIONS

### **STANDARD 8 PIN TO-3**



NOTE: ESD triangle ( $\Delta$ ) on top of package denotes pin 1 location.





PIN DIAMETER:
PIN LENGTH:
PIN MATERIAL, STD:
PIN MATERIAL, MIL:
PACKAGE:
WEIGHT:
ISOLATION:
SOCKETS:
CAGE JACKS:
HEATSINKS:

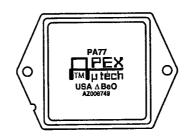
.967/1.07mm or .038/.042\*
11.4/12.7mm or .450/.500\*
Nickel plated alloy 52, solderable
Gold plated alloy 52, solderable
Hermetic, nickel plated steel
15 grams or .53 ounces
500VDC any pin to case
APEX PN: MS03
APEX PN: MS03
APEX PN: HS01 thru HS05

# **CAUTION**

Recommended mounting torque is 4 – 7 in•lbs (.45 – .79 N•m)

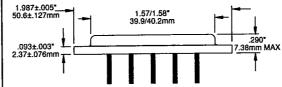
# **POWER PD10**

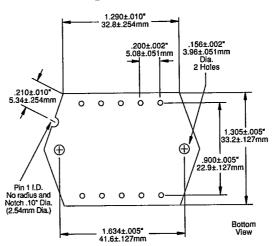
T-90-20



NOTE: Notch on package base denotes pin 1 location.

#### PD10/60S





PIN DIAMETER:
PIN LENGTH:
PIN MATERIAL, STD:
PACKAGE:
WEIGHT:
ISOLATION:
CAGE JACKS:

1.47/1.58mm or .058/.062" 11.4/12.7mm or .450/.500" Nickel plated steel Hermetic, nickel plated steel 36 grams or 1.27 ounces 500VDC any pin to case MS04 (Set of 12)

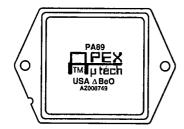
# **CAUTION**

Recommended mounting torque is 8 – 10 in lbs (.90 – 1.13 N·m)

# PACKAGE OUTLINE DIMENSIONS

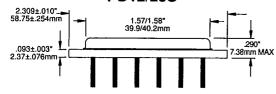
# T-90-20

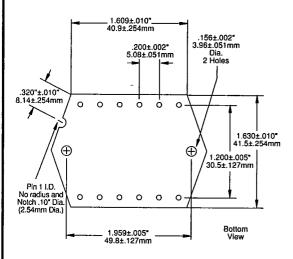
# **HIGH VOLTAGE PD12**



NOTE: Notch on package base denotes pin 1 location.

# PD12/25S





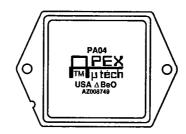
PIN DIAMETER: PIN LENGTH: PIN MATERIAL, STD: PACKAGE: WEIGHT: ISOLATION:

.585/.687mm or .023/.027" 11.4/12.7mm or .450/.500" Nickel plated steel Hermetic, nickel plated steel 53 grams or 1.87 ounces 1200VDC any pin to case

# **CAUTION**

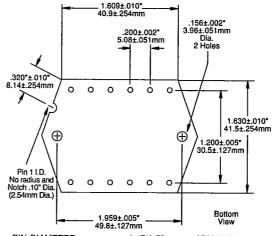
Recommended mounting torque is 8 - 10 in•lbs (.90 - 1.13 N•m)

# **HIGH POWER PD12**



NOTE: Notch on package base denotes pin 1 location.

# PD12/60S & PD12/60C 2.309±.010". 58.75±.254mi 1.57/1.58" 39.9/40.2mm (See Below) .093±.003" I 2.37±.076mm<sub>T</sub>



PIN DIAMETER: PIN LENGTH:

1.47/1.58mm or .058/.062\* 11.4/12.7mm or .450/.500"

PIN MATERIAL, STD: ISOLATION:

HEIGHT:

STD: Nickel plated steel
PD12/60S: 500VDC any pin to case
PD12/60C: 300VDC any pin to case
PD12/60C: 300VDC any pin to case
PD12/60S: 7.38mm or .290" MAX
PD12/60S: Hermetic, nickel plated steel

PACKAGE:

PD12/60C: Base: Nickel plated copper PD12/60C: Cap: Hermetic, nickel plated steel PD12/60C: Cap: Hermetic, nickel plated steel PD12/60C: 53 grams or 1.87 ounces PD12/60C: 58 grams or 2.05 ounces Apex PN: MS04 (Set of 12)

WEIGHT:

CAGE JACKS:

HEAT SINKS: Apex PN: H. MATING SOCKET: Apex PN: HS06

CAUTION

Recommended mounting torque is 8-10 in lbs (.90-1.13 N·m)